

Yogesh Sharma

List of Publications by Year in descending order

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25
papers

477
citations

687363

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22
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all docs

25
docs citations

25
times ranked

829
citing authors

#	ARTICLE	IF	CITATIONS
1	High Entropy Oxide Relaxor Ferroelectrics. ACS Applied Materials & Interfaces, 2022, 14, 11962-11970.	8.0	26
2	Magnetic Texture in Insulating Single Crystal High Entropy Oxide Spinel Films. ACS Applied Materials & Interfaces, 2021, 13, 17971-17977.	8.0	24
3	Tuning magnetic and optical properties through strain in epitaxial LaCrO ₃ thin films. Applied Physics Letters, 2021, 119, .	3.3	4
4	Self-Assembled Room Temperature Multiferroic BiFeO ₃ /LiFe ₅ O ₈ Nanocomposites. Advanced Functional Materials, 2020, 30, 1906849.	14.9	14
5	Structural and Optical Properties of Phase-Pure UO ₂ , U ₃ O ₈ , and U ₃ O ₇ Epitaxial Thin Films Grown by Pulsed Laser Deposition. ACS Applied Materials & Interfaces, 2020, 12, 35232-35241.	8.0	27
6	Substrate oxygen sponge effect: A parameter for epitaxial manganite thin film growth. Applied Physics Letters, 2020, 117, .	3.3	10
7	Thickness and strain dependence of piezoelectric coefficient in BaTiO ₃ thin films. Physical Review Materials, 2020, 4, .	2.4	20
8	Competing phases in epitaxial vanadium dioxide at nanoscale. APL Materials, 2019, 7, .	5.1	8
9	Ferroelectric Domain Studies of Patterned (001) BiFeO ₃ by Angle-Resolved Piezoresponse Force Microscopy. Scientific Reports, 2018, 8, 203.	3.3	9
10	Modulation of oxygen vacancies assisted ferroelectric and photovoltaic properties of (Nd, V) co-doped BiFeO ₃ thin films. Journal Physics D: Applied Physics, 2018, 51, 275303.	2.8	26
11	Nanoscale Control of Oxygen Defects and Metal-Insulator Transition in Epitaxial Vanadium Dioxides. ACS Nano, 2018, 12, 7159-7166.	14.6	41
12	Studies on structural, optical, magnetic, and resistive switching properties of doped BiFe _{1-x} CrxO ₃ thin films. Journal of Applied Physics, 2016, 120, .	2.5	11
13	Switchable photovoltaic and polarization modulated rectification in Si-integrated Pt/(Bi _{0.9} Sm _{0.1})(Fe _{0.97} Hf _{0.03})O ₃ /LaNiO ₃ heterostructures. Applied Physics Letters, 2015, 107, .	3.3	38
14	Disorder driven structural and dielectric properties of silicon substituted strontium titanate. Journal of Applied Physics, 2015, 118, .	2.5	5
15	Unipolar resistive switching in planar Pt/BiFeO ₃ /Pt structure. AIP Advances, 2015, 5, .	1.3	25
16	Holmium hafnate: An emerging electronic device material. Applied Physics Letters, 2015, 106, .	3.3	8
17	Non-Volatile Resistive Memory Switching in Pulsed Laser Deposited Rare-Earth Gallate-GdGaO ₃ Thin Films. ECS Transactions, 2015, 66, 287-293.	0.5	2
18	Ferroelectricity in Rare-Earth Modified Hafnia Thin Films Deposited by Sequential Pulsed Laser Deposition. ECS Solid State Letters, 2015, 4, N13-N16.	1.4	18

#	ARTICLE	IF	CITATIONS
19	Ferroelectric photovoltaic properties in doubly substituted (Bi _{0.9} La _{0.1})(Fe _{0.97} Ta _{0.03})O ₃ thin films. Applied Physics Letters, 2015, 106, .	3.3	35
20	Room temperature weak multiferroism and magnetodielectric effect in highly oriented (Y _{0.9} Bi _{0.1})(Fe _{0.5} Cr _{0.5})O ₃ thin films. Materials Research Bulletin, 2015, 68, 49-53.	5.2	7
21	Structural phase transition of ternary dielectric SmGdO ₃ : Evidence from angle dispersive x-ray diffraction and Raman spectroscopic studies. Journal of Applied Physics, 2015, 117, 094101.	2.5	9
22	Photovoltaic effect and enhanced magnetization in 0.9(BiFeO ₃)∧0.1(YCrO ₃) composite thin film fabricated using sequential pulsed laser deposition. Journal Physics D: Applied Physics, 2014, 47, 425303.	2.8	9
23	Studies of the switchable photovoltaic effect in co-substituted BiFeO ₃ thin films. Applied Physics Letters, 2014, 105, .	3.3	35
24	Phonons and magnetic excitation correlations in weak ferromagnetic YCrO ₃ . Journal of Applied Physics, 2014, 115, .	2.5	57
25	Resistive Switching and Current Conduction Mechanisms in Amorphous LaLuO ₃ Thin Films Grown by Pulsed Laser Deposition. Integrated Ferroelectrics, 2014, 157, 47-56.	0.7	3